

25 EDS Members Elected to the IEEE Grade of Fellow Effective 1 January 2013

Ramachandra Achar, Carleton University, Ottawa, ON, Canada
for contributions to interconnect and signal integrity analysis in high-speed designs

Carter Armstrong, L-3 Communications, San Carlos, CA, USA
for technical leadership in the development of high power microwave and millimeter-wave radiation sources, especially their power modules

Farrokh Ayazi, Georgia Institute of Technology, Atlanta, GA, USA
for contributions to micro-electro-mechanical resonators and resonant gyroscopes

Mansun Chan, Hong Kong University of Science and Technology, Clear Water Bay, Hong Kong
for contributions to CMOS device modeling

David Cumming, University of Glasgow, Glasgow, UK
for contributions to integrated sensors and microsystem technology

Suman Datta, Penn State University, University Park, PA, USA
for contributions to high-performance advanced silicon and compound semiconductor transistor technologies

Takatomo Enoki, Nippon Telegraph and Telephone Corporation, Atsugi-shi, Kanagawa, Japan
for contributions to compound semiconductor high speed integrated circuits for optical and wireless communication systems

David Esseni, University of Udine, Udine, Italy
for contributions to quasi-ballistic transport technology in metal oxide silicon transistors

Gerard Ghibaudo, IMEP, Grenoble, France
for contributions to electron device characterization and modeling

Kenneth Goodson, Stanford University, Stanford, CA, USA
for contributions to thermal management of electronic packaging

Kenneth Hansen, Freescale Semiconductor, Inc., Lago Vista, TX, USA
for technical leadership in wireless communications

Guifang Li, CREOL, University of Central Florida, Orlando, FL, USA
for contributions to all-optical signal processing and high-capacity fiber-optic transmission

Carlos Mazure, SOITEC, Bernin, France
for leadership in the field of silicon on insulator and memory technologies

Gaudenzio Meneghesso, University of Padova, Padova, Italy
for contributions to the reliability physics of compound semiconductors devices

Subhasish Mitra, Stanford University, Stanford, CA, USA
for contributions to design and test of robust integrated circuits

Arthur Morris, wiSpry, Inc., Raleigh, NC, USA
for development and commercialization of CMOS radio frequency micro electro-mechanical systems

Masaaki Niwa, University of Tsukuba Frontier Science, Tsukuba Ibaraki, Japan
for contributions to CMOS technology using high dielectric constant materials and metal gate

David Perreault, Massachusetts Institute of Technology, Cambridge, MA, USA
for contributions to design and application of very high frequency power electronic converters

Kameshwar Poolla, University of California, Berkeley, Berkeley, CA, USA
for contributions to system identification, robust control, and applications to semiconductor manufacturing

John Robertson, Cambridge University, Cambridge, UK
for contributions to the understanding of high-k dielectrics and metal gate electrodes for CMOS technology

John Spargo, Northrop Grumman Corporation, Redondo Beach, CA, USA
for leadership in superconducting electronics and related technologies

Randhir Thakur, Applied Materials, Fremont, CA, USA
for leadership in development and implementation of single-wafer technology in semiconductor manufacturing

Thomas Theis, IBM T.J. Watson Research Center, Yorktown Heights, NY, USA
for leadership in the development of semiconductor technologies

Peide Ye, Purdue University, West Lafayette, IN, USA
for contributions to compound semiconductor MOSFET materials and devices

Chen-Hua Yu, Taiwan Semiconductor Manufacturing Company (TSMC), Hsin-Chu County, Taiwan
for leadership in development of interconnect technology for integrated circuits

Leda Lunardi
2013 EDS Fellows Chair
North Carolina State University
Raleigh, NC, USA